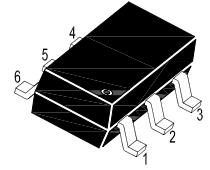
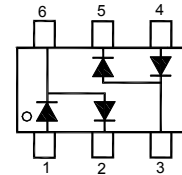


■ Silicon Epitaxial Planar Switching Diode

Fast Switching Diode



1. A1 2. C1 3. AC2
4. A2 5. C2 6. AC1

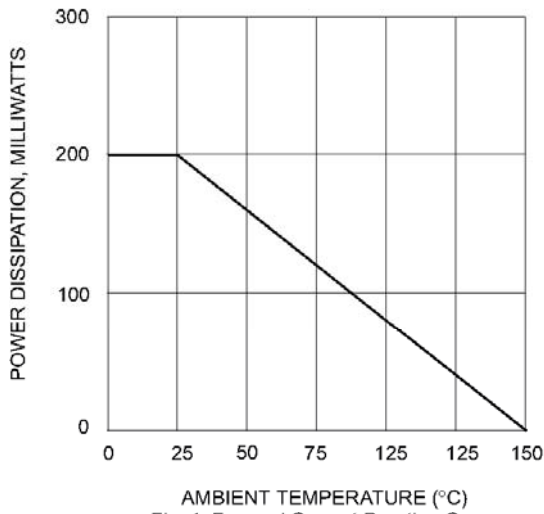
■ Simplified outline(SOT-363)

Absolute Maximum Ratings (T_a = 25 °C)

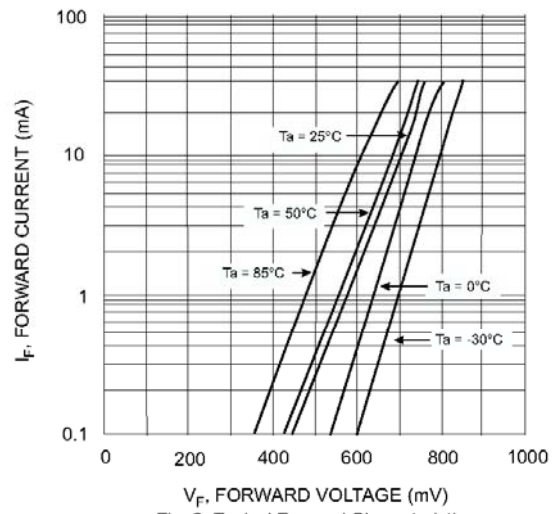
Parameter	Symbol	Value	Unit
Peak Reverse Voltage	V _{RM}	100	V
Reverse Voltage	V _R	80	V
Average Rectified Forward Current	I _{F(AV)}	150	mA
Forward Continuous Current	I _{FM}	300	mA
Non-Repetitive Peak Forward Surge Current (at t = 1 μs)	I _{FSM}	0.5	A
Power Dissipation	P _d	200	mW
Junction Temperature	T _j	150	°C
Storage Temperature Range	T _{stg}	- 65 to + 150	°C

Characteristics at T_a = 25 °C

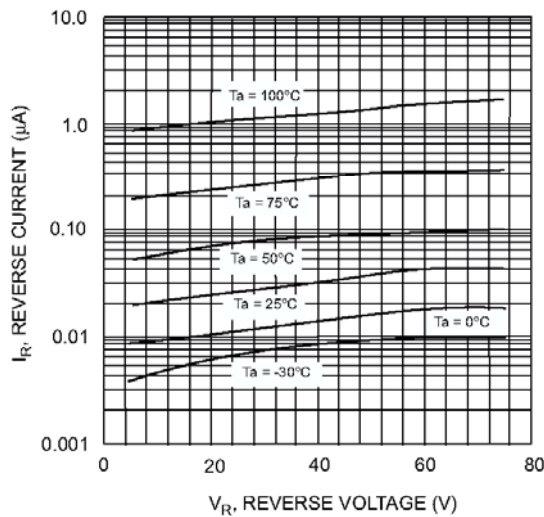
Parameter	Symbol	Min.	Max.	Unit
Forward Voltage at I _F = 5 mA at I _F = 10 mA at I _F = 100 mA at I _F = 150 mA	V _F	0.62 - - -	0.72 0.855 1 1.25	V
Reverse Leakage Current at V _R = 80 V at V _R = 20 V at V _R = 75 V, T _J = 150 °C at V _R = 25 V, T _J = 150 °C	I _R	- - - -	100 25 50 30	nA nA μA μA
Reverse Breakdown Voltage at I _R = 100 μA	V _{(BR)R}	80	-	V
Total Capacitance at V _R = 0.5 V, f = 1 MHz	C _{tot}	-	4	pF
Reverse Recovery Time at I _F = I _R = 10 mA, I _{rr} = 0.1 X I _R , R _L = 100 Ω	t _{rr}	-	4	ns



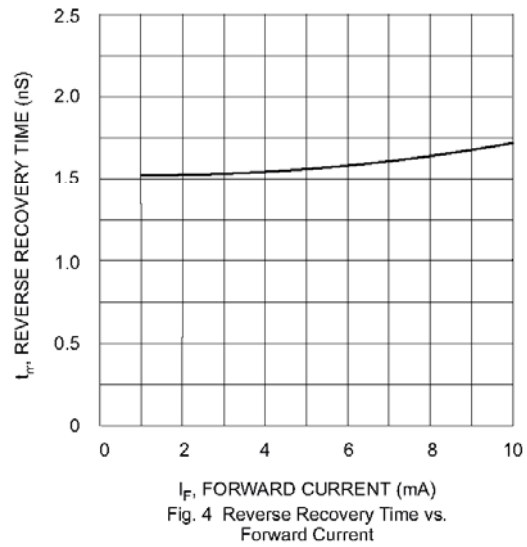
AMBIENT TEMPERATURE (°C)
Fig. 1 Forward Current Derating Curve



V_F , FORWARD VOLTAGE (mV)
Fig. 2 Typical Forward Characteristics

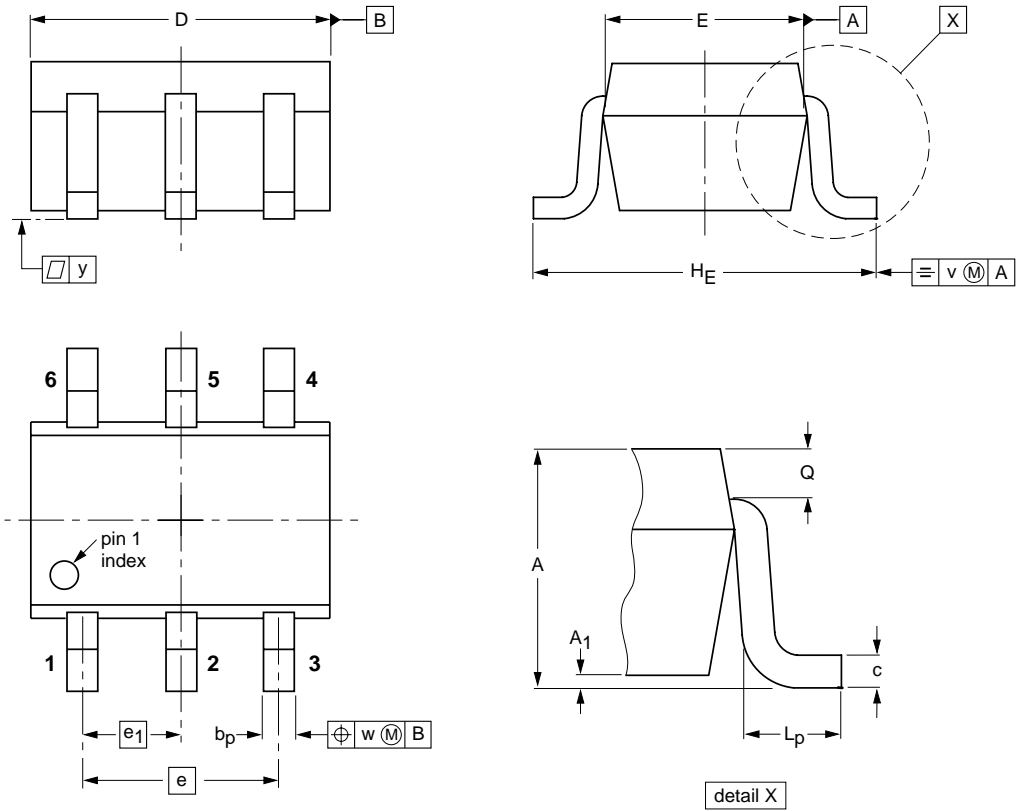


V_R , REVERSE VOLTAGE (V)
Fig. 3 Typical Reverse Characteristics



I_F , FORWARD CURRENT (mA)
Fig. 4 Reverse Recovery Time vs. Forward Current

Package Outline SOT-363



DIMENSIONS (mm are the original dimensions)

UNIT	A	A ₁ max	b _p	c	D	E	e	e ₁	H _E	L _p	Q	v	w	y
mm	1.1 0.8	0.1	0.30 0.20	0.25 0.10	2.2 1.8	1.35 1.15	1.3	0.65	2.2 2.0	0.45 0.15	0.25 0.15	0.2	0.2	0.1

Summary of Packing Options

Package	Package Description	Packing Quantity	Industry Standard
SOT-363	Tape/Reel, 7" reel	3000	EIA-481-1